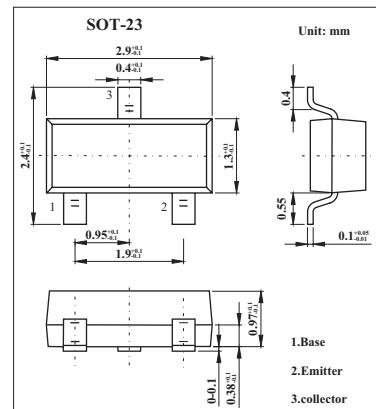


NPN Medium Frequency Transistor

BF840

■ Features

- Low current (max. 25 mA).
- Low voltage (max. 40 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	40	V
Collector-emitter voltage	V _{CEO}	40	V
Emitter-base voltage	V _{EBO}	4	V
Collector current	I _C	25	mA
Peak collector current	I _{CM}	25	mA
Total power dissipation *	P _{tot}	250	mW
Storage temperature	T _{tsg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	R _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient *	R _{th j-a}	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	I _E = 0; V _{CB} = 20 V			100	nA
Emitter cutoff current	I _{EBO}	I _C = 0; V _{EB} = 4 V			100	nA
DC current gain	h _{FE}	I _C = 1 mA; V _{CE} = 10 V	67		222	
Base to emitter voltage	V _{BE}	I _C = 1 mA; V _{CE} = 10 V	675	725	775	mV
Feedback capacitance	C _{re}	I _C = 0; V _{CB} = 10 V; f = 1 MHz		0.3		pF
Transition frequency	f _T	I _C = 1 mA; V _{CE} = 10 V; f = 100 MHz		380		MHz

■ Marking

Marking	NC
---------	----